

IN THE SPECIFICATION

Please amend the title to read as follows. Applicant includes herewith an Attachment for Specification Amendments showing a marked up version of the original title.

SEMICONDUCTOR DEVICE WITH SEMICONDUCTOR CHIP SUPPORT
STRUCTURE

IN THE CLAIMS

A. Cancelled Claims

Please cancel Claims 3, 4, and 9-11 without prejudice or disclaimer of the subject matter contained therein.

B. Amended Claims

Please amend the claims in accordance with the following rewritten claims in clean form. Applicant includes herewith an Attachment for Claim Amendments showing a marked up version of each amended claim.

1. (Twice Amended) A semiconductor device comprising:
 - a first semiconductor chip mounted on a substrate;
 - a second semiconductor chip directly mounted on the first semiconductor chip with an adhesive, the second semiconductor chip extending beyond a perimeter of the first semiconductor chip; and

a base member disposed between the second semiconductor chip and the substrate, said base member being laterally spaced apart from the first semiconductor chip;

wherein the second semiconductor chip is supported by the base member.

2. (Twice Amended) A semiconductor device comprising:

a first semiconductor chip mounted on a substrate;

a second semiconductor chip directly mounted on the first semiconductor chip with an adhesive, the second semiconductor chip extending beyond a perimeter of the first semiconductor chip; and

a non-compliant filler layer provided between the second semiconductor chip and the substrate;

wherein the second semiconductor chip is supported by the filler layer.

5. (Amended) A semiconductor device according to claim 1, wherein said second semiconductor chip includes peripheral portions extending beyond said perimeter of said first semiconductor chip which are supported by said base member.

6. (Amended) A semiconductor device according to Claim 1, wherein said base member further comprises a frame shaped member surrounding said first semiconductor chip.

7. (Amended) A semiconductor device according to Claim 1, wherein said base member further comprises columnar shaped members disposed about said perimeter of said first semiconductor chip.

C. New Claims

Please add the following new claims.

12. (New) The semiconductor device of Claim 1 wherein a size of a surface area of said base member contacting said second semiconductor chip is substantially equal to a size of a surface area of the first semiconductor chip contacting said second semiconductor chip.

13. (New) The semiconductor device of Claim 1 wherein said base member includes a surface contacting said second semiconductor chip, a portion of said surface extending beyond an outboard edge of said second semiconductor chip.

14. (New) The semiconductor device of Claim 1 further comprising a sealing resin disposed between said base layer and said first semiconductor chip.

15. (New) The semiconductor device of Claim 1 wherein said base member has a coefficient of thermal expansion which is different from a coefficient of thermal expansion of at least one of said first and second semiconductor chips.

16. (New) The semiconductor device of Claim 2 wherein said filler layer further comprises a thermosetting resin.

17. (New) The semiconductor device of Claim 2 wherein said filler layer further comprises a non-conduction material.

18. (New) The semiconductor device of Claim 17 wherein said filler layer further comprises a die-bonding material.

19. (New) The semiconductor device of Claim 2 wherein a size of a surface area of said filler layer contacting said second semiconductor chip is substantially equal to a size of a surface area of the first semiconductor chip contacting said second semiconductor chip.

20. (New) The semiconductor device of Claim 2 wherein a size of a surface area of said filler layer contacting said second semiconductor chip is greater than a size of a surface area of the first semiconductor chip contacting said second semiconductor chip.

21. (New) The semiconductor device of Claim 2 wherein said filler layer includes a portion disposed between said first semiconductor chip and said substrate.

22. (New) The semiconductor device of Claim 21 wherein a viscosity of said portion of said filler layer disposed between said first semiconductor chip and said substrate is lower than a viscosity of another portion of said filler layer disposed outboard of said first semiconductor chip between said second semiconductor chip and said substrate.